

a 2016 0074

The invention relates to semiconductor technology and can be used in solar radiation conversion devices.

The method for growth of $n^+p^-p^+$ InP structure for solar cells comprises growth of epitaxial layer pInP on p^+ InP substrates with the crystallographic orientation (100), the disorientation of $3...5^\circ$ toward (110) and the charge carrier concentration of $1...3 \cdot 10^{18} \text{ cm}^{-3}$, growth of epitaxial layer n^+ InP and deposition of ohmic contacts. The n^+ InP layer is grown after the gas etching of the reactor and the epitaxial layer pInP.

Claims: 1